# **MGFC36V4450A**

### 4.4 ~ 5.0GHz BAND 4W INTERNALLY MATCHED GaAs FET

## **DESCRIPTION**

The MGFC36V4450A is an internally impedance-matched GaAs power FET especially designed for use in 4.4 ~ 5.0 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

#### **FEATURES**

Class A operation
Internally matched to 50(ohm) system
High output power
P1dB = 4W (TYP.) @ f=4.4~5.0GHz
High power gain
GLP = 12 dB (TYP.) @ f=4.4~5.0GHz
High power added efficiency
P.A.E. = 32 % (TYP.) @ f=4.4~5.0GHz
Low distortion [ item -51 ]
IM3= -45 dBc(TYP.) @Po=25dBm S.C.L.

## **APPLICATION**

item 01: 4.4~5.0 GHz band power amplifier

item 51: 4.4~5.0 GHz band digital radio communication

#### **QUALITY GRADE**

IG

## RECOMMENDED BIAS CONDITIONS

VDS = 10(V)

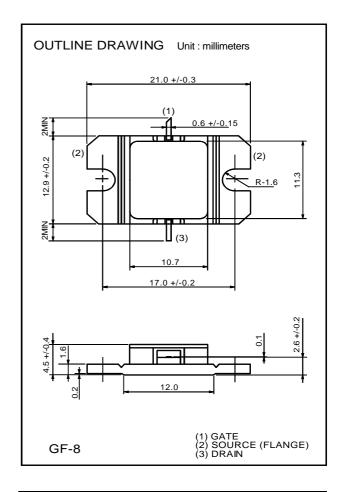
ID = 1.2(A) Refer to Bias Procedure

RG= 100 (ohm)

## ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage	ate to drain voltage -15		
VGSO	Gate to source voltage	-15	V	
ID	Drain current	3.75	Α	
IGR	Reverse gate current	-10	mA	
IGF	Forward gate current	current 21		
PT	Total power dissipation *1	25	W	
Tch	Channel temperature	175	175 deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	

<sup>\*1 :</sup> Tc=25 deg.C



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## **ELECTRICAL CHARACTERISTICS** (Ta=25 deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
Symbol	Falailletei		Min.	Тур.	Max.	Offic
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	-	3.75	Α
gm	Transconductance	VDS=3V, ID=1.1A	-	1	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=10mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression		35	37	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=1.2A, f=4.4~5.0GHz	9	12	-	dB
ID	Drain current		-	=.	1.8	Α
P.A.E.	Power added efficiency		-	32	-	%
IM3	3rd order IM distortion *1		-42	-45	-	dBc
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	5	6	deg.C/W

<sup>\*1:</sup> item -51, 2 tone test, Po=25dBm Single Carrier Level, f=5GHz, Delta f=10MHz



<sup>\*2 :</sup> Channel to case

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